

IN THE CLAIMS

Please cancel claims 45 and 48 without prejudice to their consideration in a continuing application.

Please amend claims 34, 36, 37, 44, 46 and 47 as follows:

C1
34. (Currently Amended) A low resistance ITO thin film having a resistivity less than $1 \times 10^{-4} \Omega \text{ cm}$, said film deposited on a single crystalline substrate by epitaxial growth.

C2
36. (Currently Amended) A low resistance ITO thin film according to claim 34, wherein film mobility is greater than $39 \text{ cm}^2/\text{Vs}$.

37. (Currently Amended) A substrate having a low resistant ITO thin film comprising:

a single crystalline substrate; and

a low resistance ITO thin film having a resistivity lower than $1 \times 10^{-4} \Omega \text{ cm}$ deposited on said single crystalline substrate by epitaxial growth.

C3

44. (Currently Amended) A substrate having a low resistant ITO thin film according to claim 37, wherein said single crystal substrate is provided to accept an In_2O_3 crystal structure deposited thereon.

C4

46. (Currently Amended) A substrate having a low resistant ITO thin film according to claim 37, wherein said single crystalline substrate is one of a YSZ single crystal substrate, a substrate on which a C-axis oriented ZnO thin film is formed, a sapphire substrate, a SiC single crystal substrate and a silicon single crystal substrate.

47. (Currently Amended) A substrate having a low resistant ITO thin film according to claim 37, wherein said single crystalline substrate has a C axis oriented ZnO film formed thereon.